

Lithography-Free Nanowire Transistors

A method for large production of high-performance nanowires using a bottom-up approach

Georgia Tech inventors have developed a fabrication method competent for large production scale that is entirely “bottom-up” for MOSFETs. This approach builds the layers of nanowires from the bottom up, as opposed to removing material from a bulk sample, as in the top-down fabrication method. This fabrication method utilizes the single crystallinity of semiconductor nanowires to provide high electron carrier motilities and bottom-up nanowire growth to achieve the chemical structure needed for the nanowires. This approach allows for large-scale fabrication and patterning of high-performance nanowires. When utilized in MOSFETs the nanowires allow for exceptional device switching speeds at low voltages.

Summary Bullets

- **Scalable** – Eliminating the cost and time associated with top-down patterning enables large-scale manufacturing
- **High Performance** – Achieves switching speeds well beyond 1 GHz at supply voltages near 0.5 V
- **Adaptable** – Device dimensions can be readily scaled as transistor fabrication techniques advance

Solution Advantages

- **Scalable** – Eliminating the cost and time associated with top-down patterning enables large-scale manufacturing
- **High Performance** – Achieves switching speeds well beyond 1 GHz at supply voltages near 0.5 V
- **Adaptable** – Device dimensions can be readily scaled as transistor fabrication techniques advance

Potential Commercial Applications

- Artificial skins
- Smart structures
- Smart dust – A simple computer light enough to be suspended in air formed from electronic systems
- Electronic medicines

Background and More Information

Applications ranging from artificial skins to smart structures are demanding a fundamentally new electronics manufacturing system due to a long-standing trade-off between the performance and manufacturing scale of

electronics. Production of active devices; circuit components capable of controlling current such as metal oxide semiconductor field effect transistors (MOSFETs), either exhibit high performance or large production scale, but not both. A manufacturing system, enabling large production or high-performance MOSFETs, is crucial to the development of electronic applications.

Inventors

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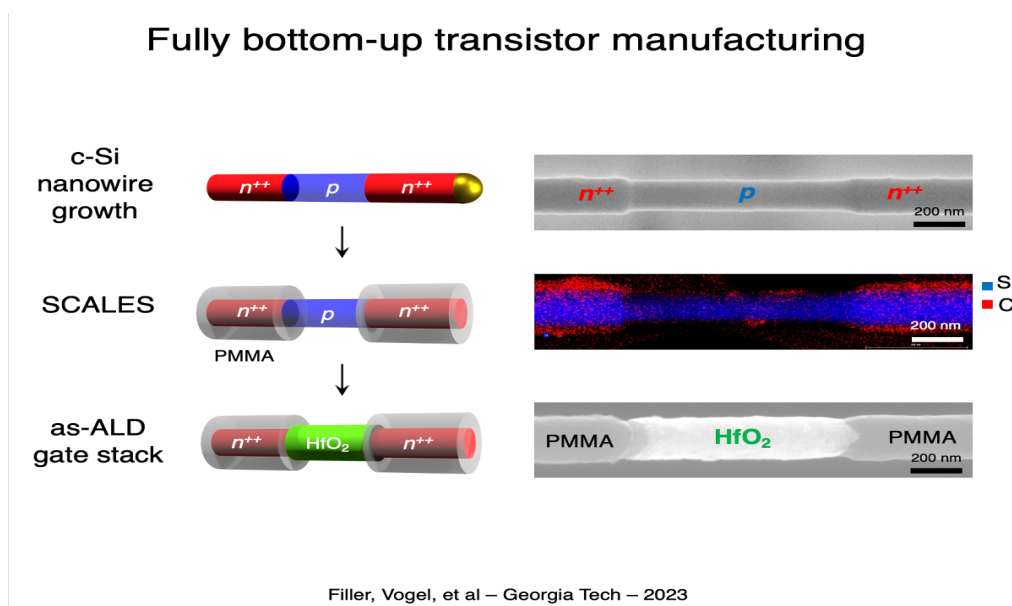
IP Status

<p>The following patent has issued, and additional coverage is pending</p>: EP3867193A4

Publications

[Investigating wet chemical oxidation methods to form SiO₂ interlayers for self-aligned Pt-HfO₂-Si gate stacks](#),
Journal of Vacuum Science and Technology A - July 10, 2023

Images



Schematic illustration of and representative data from each step in the transistor fabrication process, including single-crystal Si nanowire growth, selective polymer masking, and area-selective atomic layer deposition (ALD).

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